

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicants	:	Sharon M. Weiss, Philippe M. Fauchet, and Michael Molinari)	Examiner:
)	To Be Assigned
Serial No.	:	To Be Assigned)	Art Unit:
)	To Be Assigned
Cnfrm. No.	:	To Be Assigned)	
Filed	:	Herewith)	
For	:	METHODS FOR THE MINIMIZATION OF THERMALLY INDUCED DRIFT OF REFLECTANCE SPECTRA IN PHOTONIC BAND-GAP DEVICES AND SYSTEMS THEREOF)	

INFORMATION DISCLOSURE STATEMENT
UNDER 37 CFR §§ 1.97-1.98

Mail Stop: Patent Application

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Dear Sir:

Pursuant to 37 CFR §§ 1.97-1.98, applicants hereby bring to the attention of the
United States Patent and Trademark Office, the enclosed references listed on the attached
PTO-1449 form.

Respectfully submitted,

Date: April 16, 2004

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Registration No. 35,584

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				Art Unit		To Be Assigned
Examiner Name		To Be Assigned				
Sheet	1	of	3	Attorney Docket Number		176/61511 (2-11144-03043)

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Examiner Initials*	Cite No. ¹	U.S. Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
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	3	US-5,740,287	04/14/1998	Scalora et al.	
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